

ABSTRACT OF THE DISCLOSURE

A method for fabricating a resin-encapsulated semiconductor device includes the steps of consecutively forming a first interconnect pattern, a dielectric film and a second interconnect

- 5 pattern on a metallic plate, mounting a semiconductor chip on the dielectric film, connecting chip electrodes of the semiconductor chip to the second interconnect pattern, encapsulating the semiconductor chip on the first dielectric film, removing the metallic plate selectively from the first interconnect pattern, and forming a
- 10 plurality of metallic bumps on the exposed bottom surface of the first interconnect pattern.

100 90 80 70 60 50 40 30 20 10 0